

N-channel 650 V, 0.09 Ω typ., 28 A MDmesh™ V Power MOSFETs
in TO-220FP, I²PAKFP, I²PAK packages

Datasheet - production data

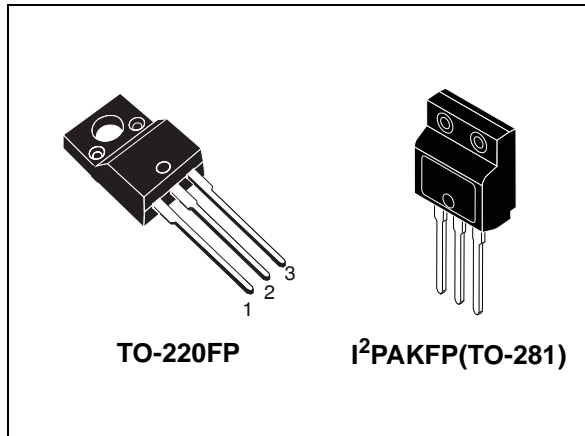
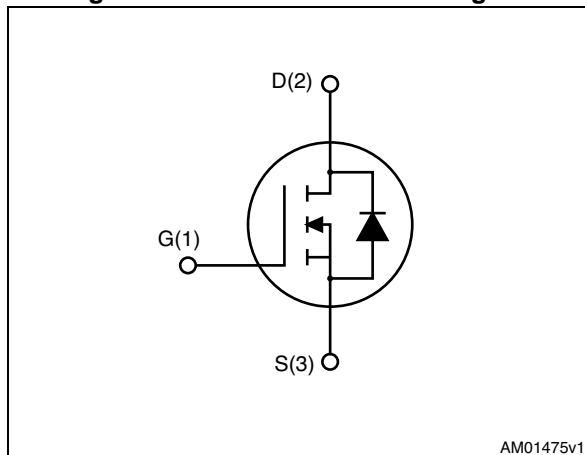


Figure 1. Internal schematic diagram



Features

Order codes	V _{DS} @ T _{Jmax}	R _{DS(on)} max	I _D
STF34N65M5	710 V	0.11 Ω	28 A
STFI34N65M5			

- Worldwide best R_{DS(on)} * area
- Higher V_{DSS} rating and high dv/dt capability
- Excellent switching performance
- 100% avalanche tested

Applications

- Switching applications

Description

These devices are N-channel MDmesh™ V Power MOSFETs based on an innovative proprietary vertical process technology, which is combined with STMicroelectronics' well-known PowerMESH™ horizontal layout structure. The resulting product has extremely low on-resistance, which is unmatched among silicon-based Power MOSFETs, making it especially suitable for applications which require superior power density and outstanding efficiency.

Table 1. Device summary

Order codes	Marking	Packages	Packaging
STF34N65M5	34N65M5	TO-220FP	Tube
STFI34N65M5		I ² PAKFP (TO-281)	

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	± 25	V
I_D	Drain current (continuous) at $T_C = 25\text{ °C}$	28 ⁽¹⁾	A
I_D	Drain current (continuous) at $T_C = 100\text{ °C}$	17.7 ⁽¹⁾	A
$I_{DM}^{(1)}$	Drain current (pulsed)	112 ⁽¹⁾	A
P_{TOT}	Total dissipation at $T_C = 25\text{ °C}$	35	W
dv/dt ⁽²⁾	Peak diode recovery voltage slope	15	V/ns
dv/dt ⁽³⁾	MOSFET dv/dt ruggedness	50	V/ns
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s; $T_C = 25\text{ °C}$)	2500	V
T_{stg}	Storage temperature	- 55 to 150	°C
T_j	Max. operating junction temperature	150	°C

- Limited by maximum junction temperature.
- $I_{SD} \leq 28\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$; $V_{DS\ peak} < V_{(BR)DSS}$, $V_{DD}=400\text{ V}$.
- $V_{DS} \leq 480\text{ V}$

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	3.57	°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient max	62.5	°C/W

Table 4. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not repetitive (pulse width limited by T_{jmax})	7	A
E_{AS}	Single pulse avalanche energy (starting $t_j=25\text{ °C}$, $I_d=I_{AR}$; $V_{dd}=50$)	510	mJ

2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified)

Table 5. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$, $V_{GS} = 0$	650			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = 650\text{ V}$ $V_{DS} = 650\text{ V}$, $T_C = 125\text{ °C}$			1 100	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 25\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $I_D = 14\text{ A}$		0.09	0.11	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 100\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$	-	2700	-	pF
C_{oss}	Output capacitance		-	75	-	pF
C_{riss}	Reverse transfer capacitance		-	6.3	-	pF
$C_{o(tr)}^{(1)}$	Equivalent capacitance time related	$V_{DS} = 0\text{ to }520\text{ V}$, $V_{GS} = 0$	-	220	-	pF
$C_{o(er)}^{(2)}$	Equivalent capacitance energy related		-	63	-	pF
R_G	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	1.95	-	Ω
Q_g	Total gate charge	$V_{DD} = 520\text{ V}$, $I_D = 14\text{ A}$, $V_{GS} = 10\text{ V}$ (see Figure 16)	-	62.5	-	nC
Q_{gs}	Gate-source charge		-	17	-	nC
Q_{gd}	Gate-drain charge		-	28	-	nC

1. Time related is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}
2. Energy related is defined as a constant equivalent capacitance giving the same stored energy as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t_d (v)	Voltage delay time	$V_{DD} = 400$ V, $I_D = 18$ A, $R_G = 4.7$ Ω , $V_{GS} = 10$ V (see Figure 17 and Figure 20)	-	59	-	ns
t_r (v)	Voltage rise time		-	8.7	-	ns
t_f (i)	Current fall time		-	7.5	-	ns
t_c (off)	Crossing time		-	12	-	ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		28	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		112	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 28$ A, $V_{GS} = 0$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 28$ A, $di/dt = 100$ A/ μ s $V_{DD} = 100$ V (see Figure 20)	-	350		ns
Q_{rr}	Reverse recovery charge		-	5.6		μ C
I_{RRM}	Reverse recovery current		-	32		A
t_{rr}	Reverse recovery time	$I_{SD} = 28$ A, $di/dt = 100$ A/ μ s $V_{DD} = 100$ V, $T_j = 150$ °C (see Figure 20)	-	422		ns
Q_{rr}	Reverse recovery charge		-	7.4		μ C
I_{RRM}	Reverse recovery current		-	35		A

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300 μ s, duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

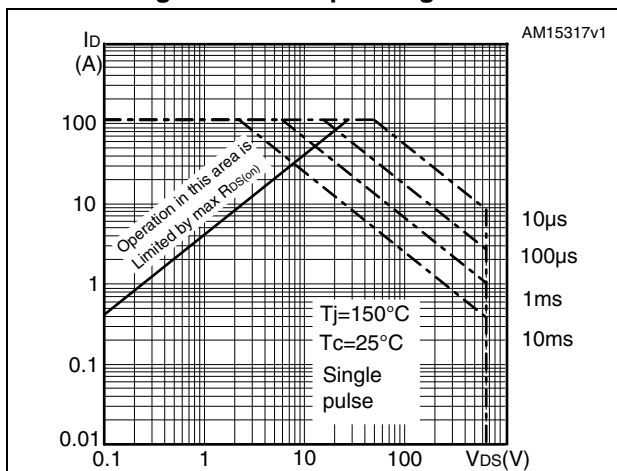


Figure 3. Thermal impedance

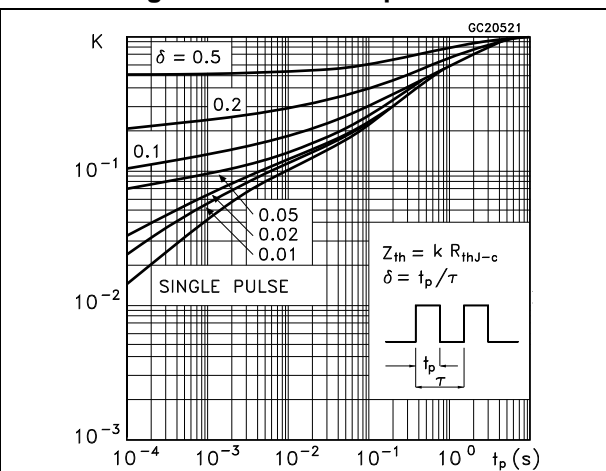


Figure 4. Output characteristics

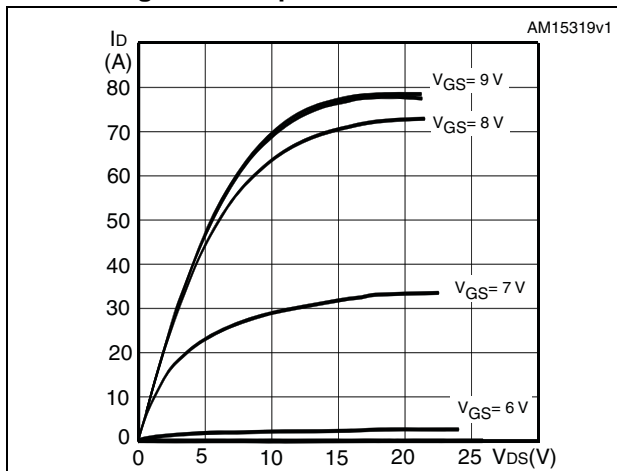


Figure 5. Transfer characteristics

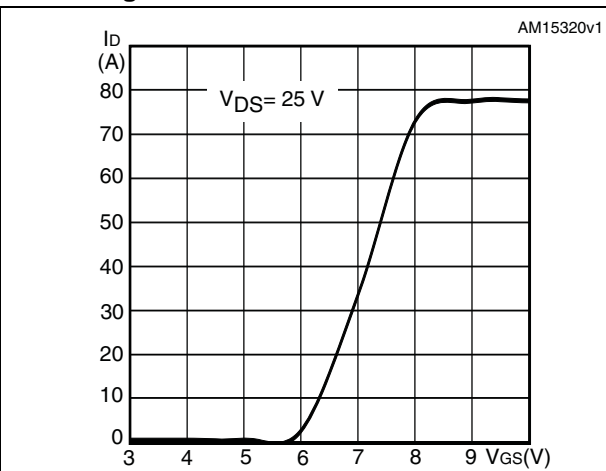


Figure 6. Gate charge vs gate-source voltage

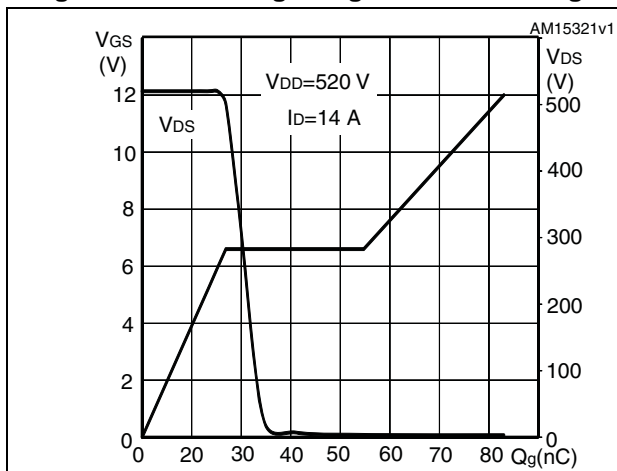


Figure 7. Static drain-source on-resistance

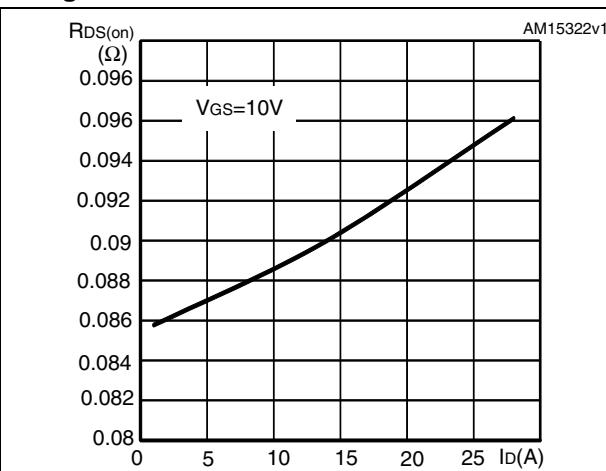


Figure 8. Capacitance variations

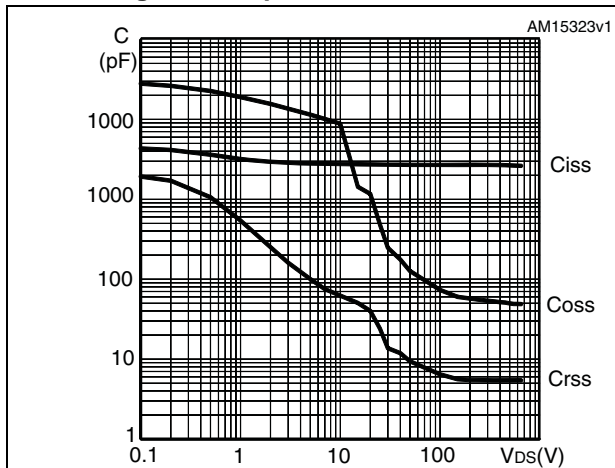


Figure 9. Output capacitance stored energy

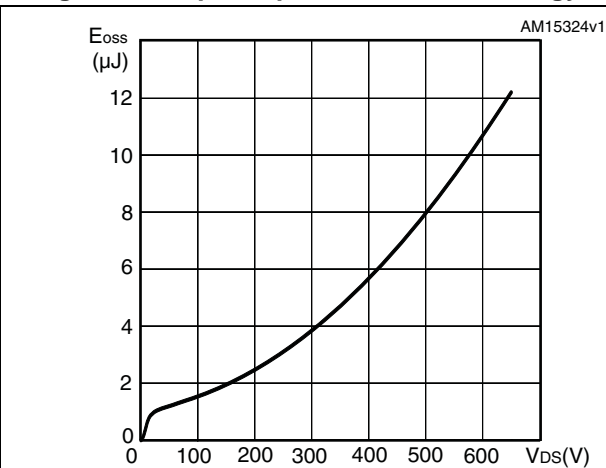


Figure 10. Normalized gate threshold voltage vs temperature

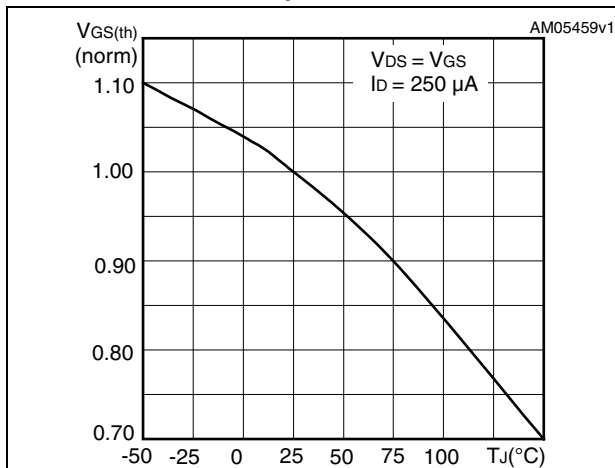


Figure 11. Normalized on-resistance vs temperature

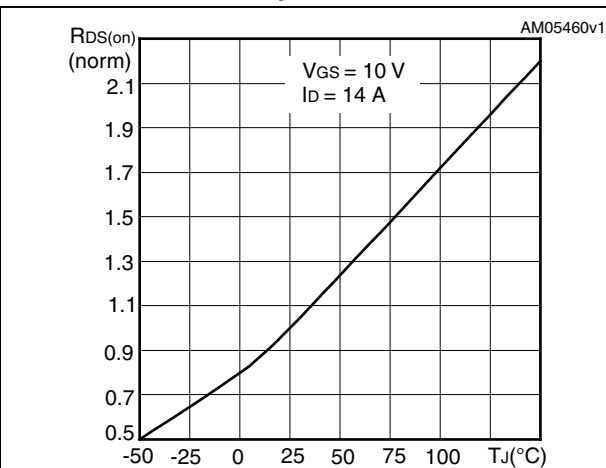


Figure 12. Source-drain diode forward characteristics

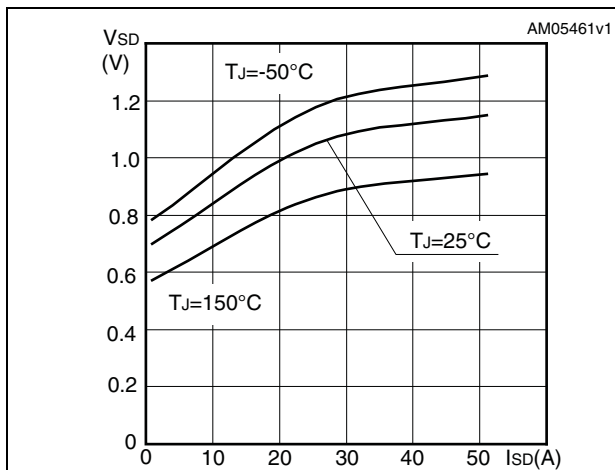


Figure 13. Normalized V_{DS} vs temperature

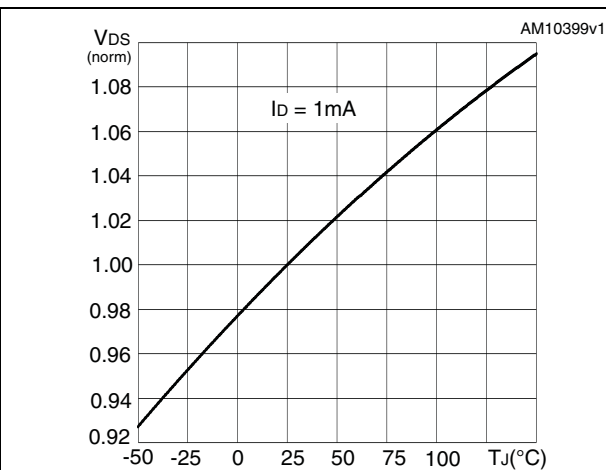
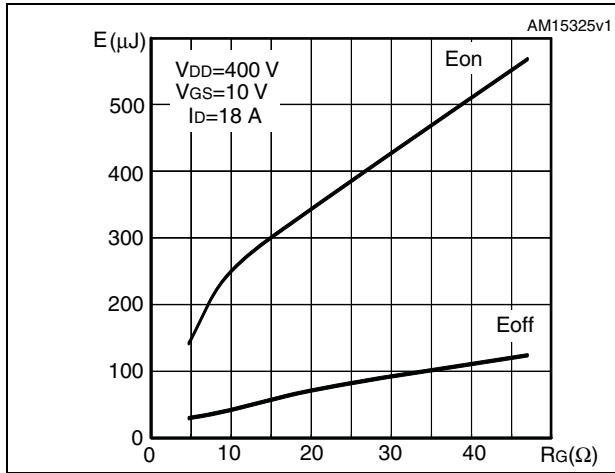


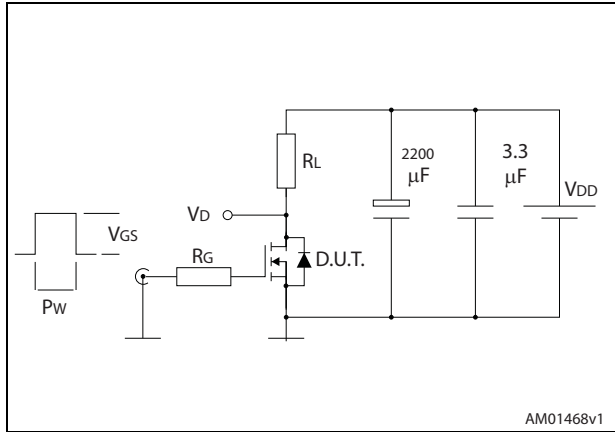
Figure 14. Switching losses vs gate resistance
(1)



1. E_{on} including reverse recovery of a SiC diode

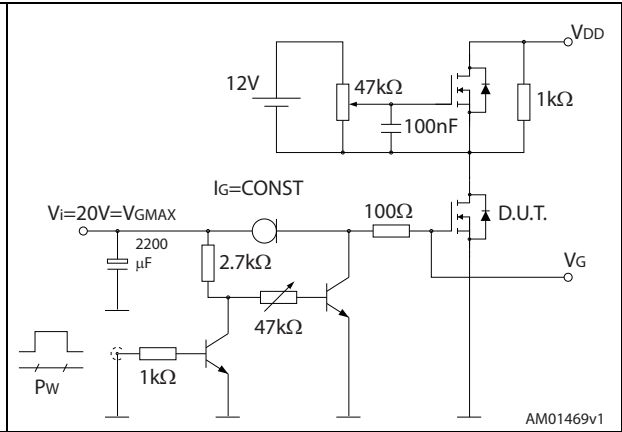
3 Test circuits

Figure 15. Switching times test circuit for resistive load



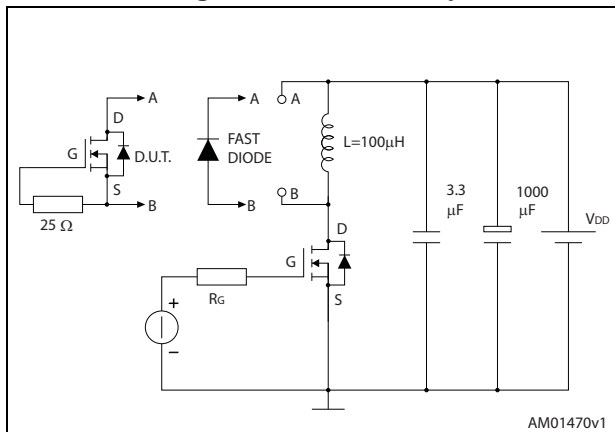
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Figure 16. Gate charge test circuit



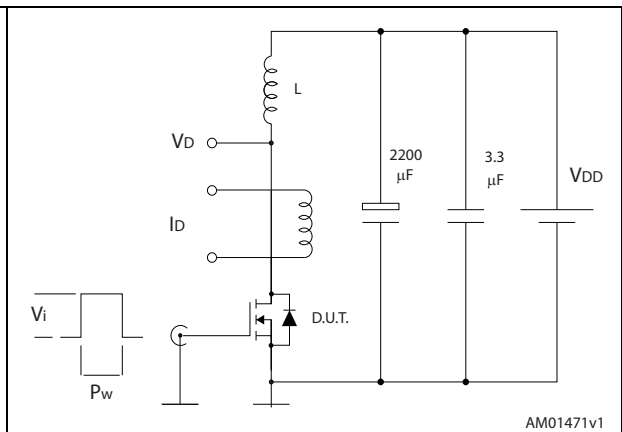
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Figure 17. Test circuit for inductive load switching and diode recovery times



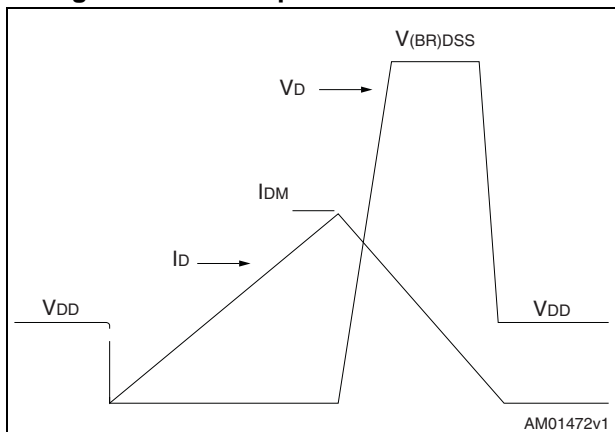
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Figure 18. Unclamped inductive load test circuit



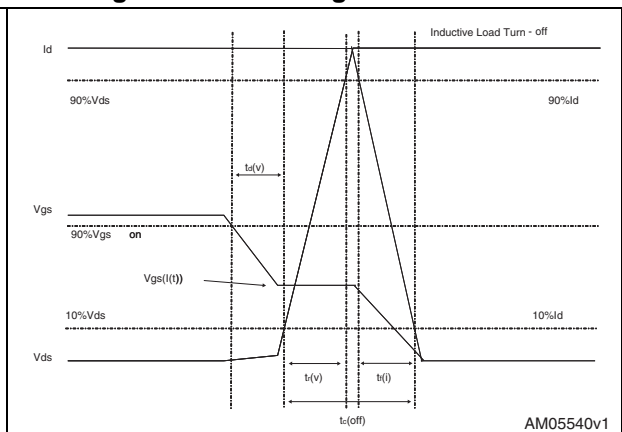
AM01471v1

Figure 19. Unclamped inductive waveform



AM01472v1

Figure 20. Switching time waveform



AM05540v1

4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Figure 21. TO-220FP drawing

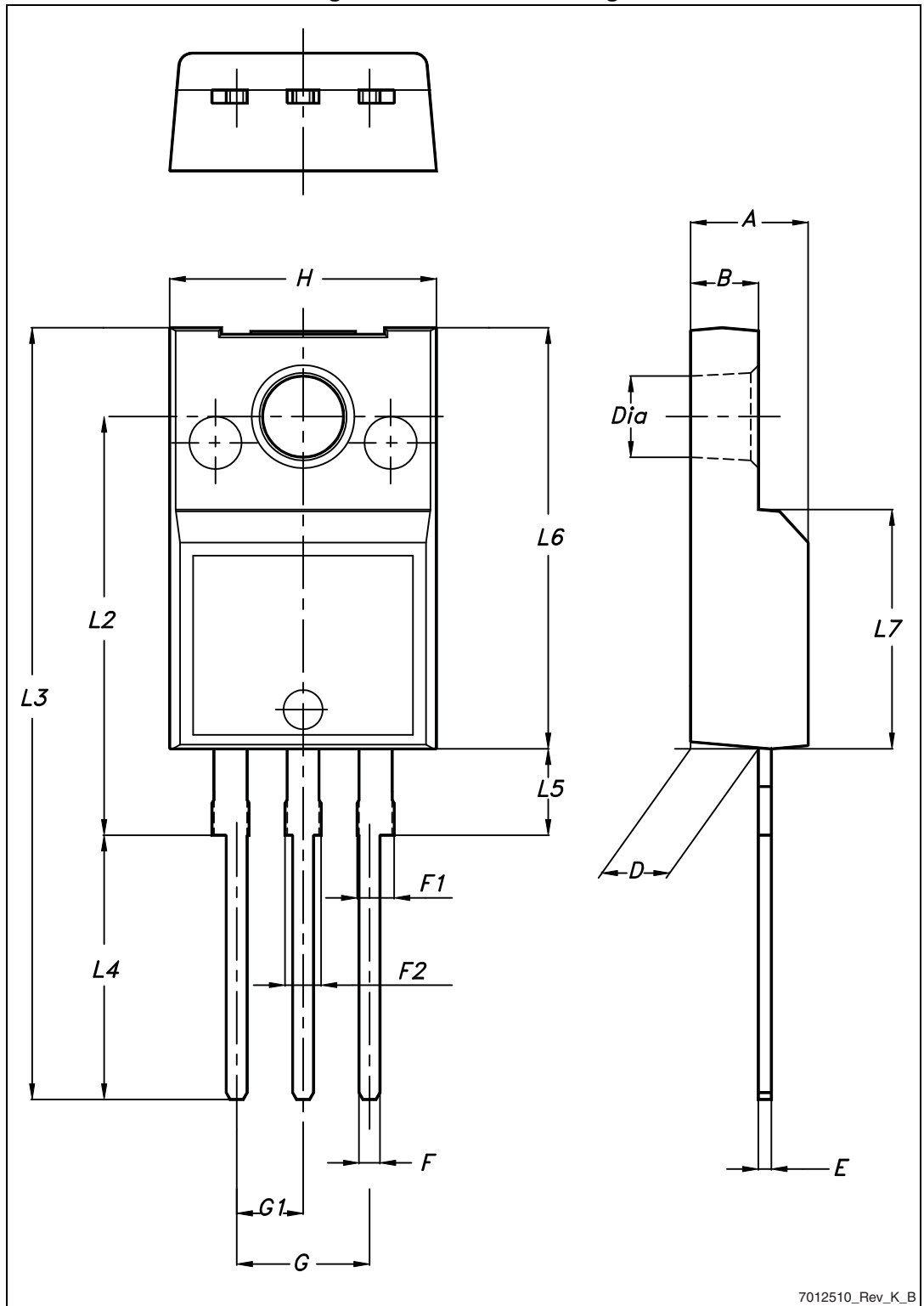


Table 9. TO-220FP mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

Figure 22. I²PAKFP (TO-281) drawing

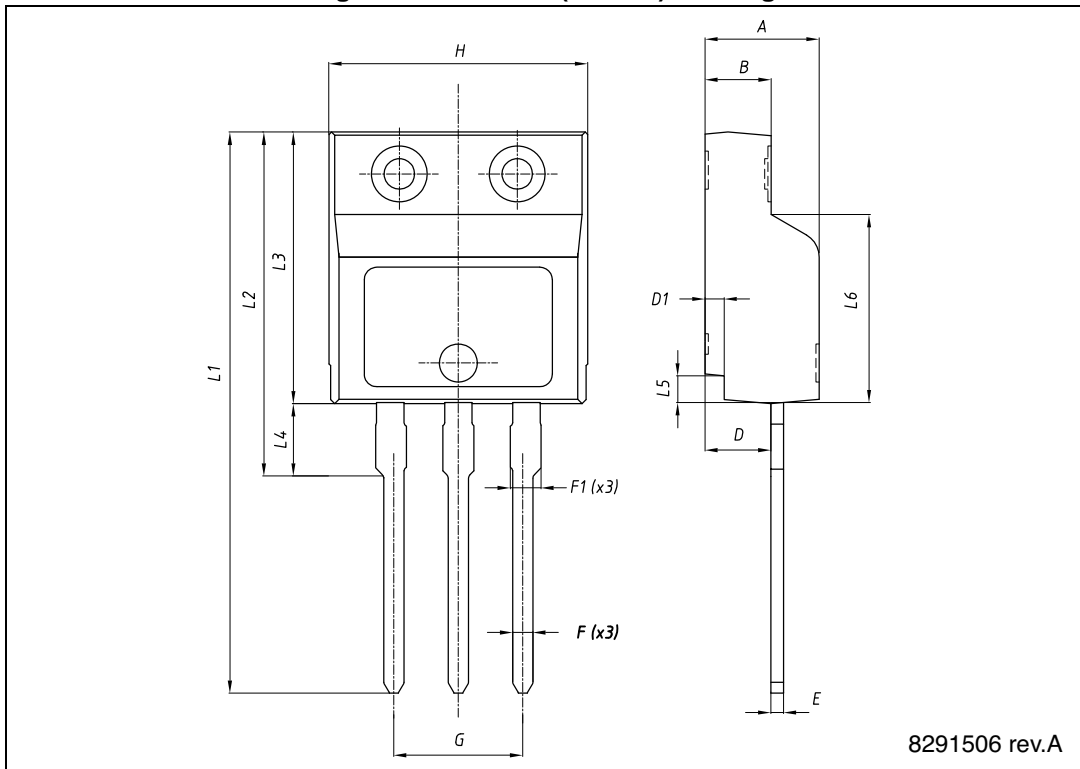


Table 10. I²PAKFP (TO-281) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
B	2.50		2.70
D	2.50		2.75
D1	0.65		0.85
E	0.45		0.70
F	0.75		1.00
F1			1.20
G	4.95	-	5.20
H	10.00		10.40
L1	21.00		23.00
L2	13.20		14.10
L3	10.55		10.85
L4	2.70		3.20
L5	0.85		1.25
L6	7.30		7.50

5 Revision history

Table 11. Document revision history

Date	Revision	Changes
14-Jan-2014	1	First release. Part numbers previously included in datasheet DocID022853

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